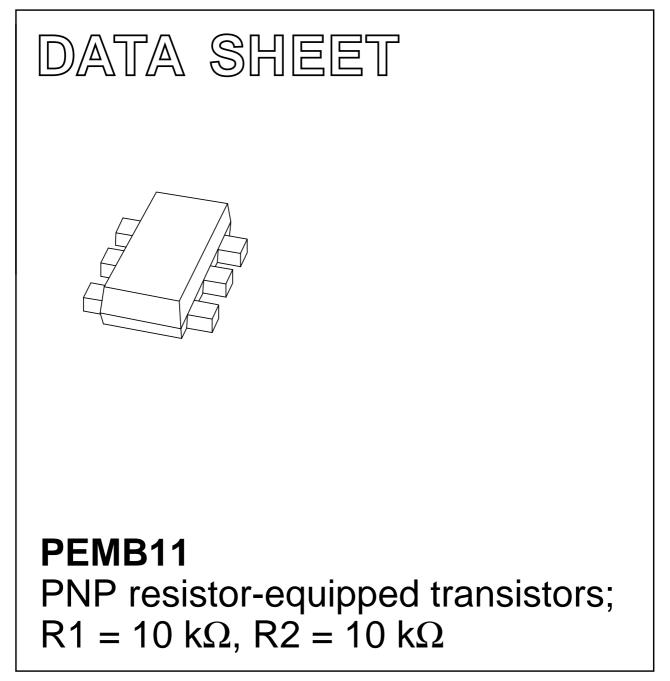
DISCRETE SEMICONDUCTORS



Preliminary specification

2001 Sep 13



PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

FEATURES

- 300 mW total power dissipation
- Very small 1.6 mm x 1.2 mm ultra thin package
- Excellent coplanarity due to straight leads
- Replaces two SC-75/SC-89 packaged transistors on same PCB area
- Reduces required PCB area
- Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

DESCRIPTION

PNP resistor-equipped transistors in a SOT666 plastic package.

MARKING

TYPE NUMBER	MARKING CODE		
PEMB11	B1		

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	-50	V
I _{CM}	peak collector current	-100	mA
TR1	PNP	_	-
TR2	PNP	—	-
R1	bias resistor	10	kΩ
R2	bias resistor	10	kΩ

PINNING

PIN		DESCRIPTION
1, 4	emitter	TR1; TR2
2, 5	base	TR1; TR2
6, 3	collector	TR1; TR2

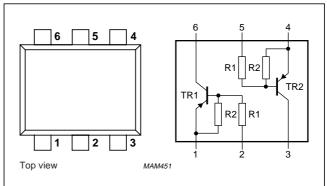


Fig.1 Simplified outline (SOT666) and symbol.

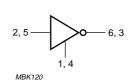


Fig.2 Equivalent inverter symbol.

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transis	stor unless otherwise specified	·	·		
V _{CBO}	collector-base voltage	open emitter	_	-50	V
V _{CEO}	collector-emitter voltage	open base	_	-50	V
V _{EBO}	emitter-base voltage	open collector	-	-10	V
VI	input voltage				
	positive		_	+10	V
	negative		-	-40	V
lo	output current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	-	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C
Per device	9		·		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	300	mW

Note

1. Transistor mounted on a FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
R _{th j-a}	thermal resistance from junction to ambient	notes 1 and 2	416	K/W	

Notes

1. Transistor mounted on an FR4 printed-circuit board.

2. The only recommended soldering method is reflow soldering.

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PEMB11

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

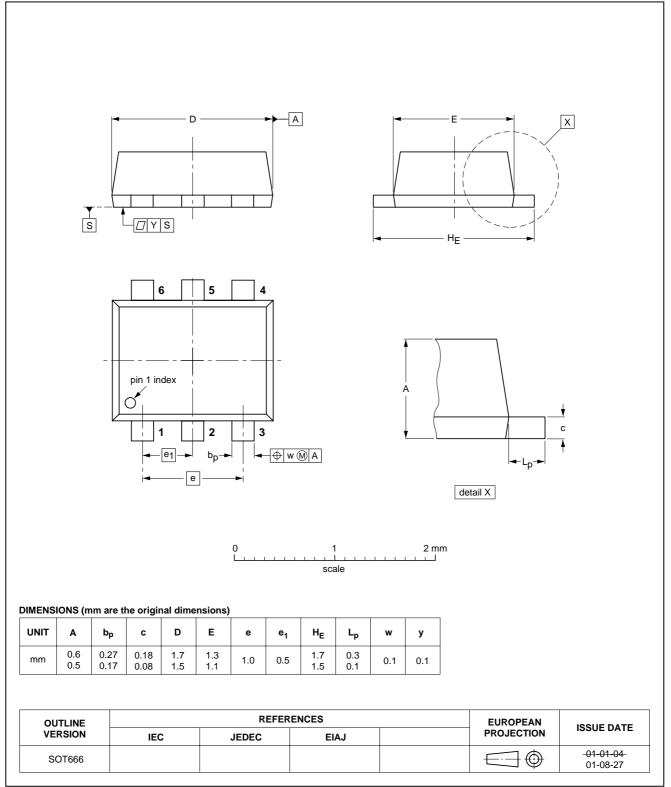
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transis	Per transistor unless otherwise specified					
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; \text{ I}_{C} = 0$	-	-	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -50 \text{ V}; I_B = 0$	-	-	-1	μA
		$V_{CE} = -30 \text{ V}; I_B = 0; T_j = 150 ^{\circ}\text{C}$	-	-	-50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0$	-	-	-400	μA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -5 \text{ mA}$	30	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{\rm C} = -10$ mA; $I_{\rm B} = -0.5$ mA	-	-	-150	mV
V _{i(off)}	input off voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	_	-1.1	-0.8	V
V _{i(on)}	input on voltage	$V_{CE} = -0.3 \text{ V}; I_C = -10 \text{ mA}$	-2.5	-1.8	-	V
R1	input resistor		7	10	13	kΩ
R2 R1	resistor ratio		0.8	1.0	1.2	kΩ
Cc	collector capacitance	$I_E = I_e = 0; V_{CB} = -10 V; f = 1 MHz$	-	-	3	pF

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PACKAGE OUTLINE





SOT666

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

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DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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PEMB11

NOTES

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